Abstracts

10.6 Gbit/s 2:1 Time Division Multiplexer Using Dual Gate GaAs MESFETs

Q.Z. Liu. "10.6 Gbit/s 2:1 Time Division Multiplexer Using Dual Gate GaAs MESFETs." 1990 MTT-S International Microwave Symposium Digest 90.2 (1990 Vol. II [MWSYM]): 889-892.

A 2:1 time division multiplexer (MUX) has been designed and built with dual gate GaAs MESFETs in thick film circuits. 10.6 Gbit/s NRZ pulses have been obtained. The voltage swing of MUX at 10 Gbit/s is 1V which is the largest one reported so far. The operation of MUX has been simulated by using mwSPICE and a good agreement between the measured and simulated switching waveforms has been obtained.

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